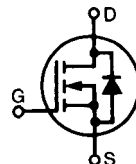


HiPerFET™ Power MOSFET

IXFH 22N55

$V_{DSS} = 550 \text{ V}$
 $I_{D(\text{cont})} = 22 \text{ A}$
 $R_{DS(\text{on})} = 0.27 \Omega$
 $t_{rr} \leq 250 \text{ ns}$

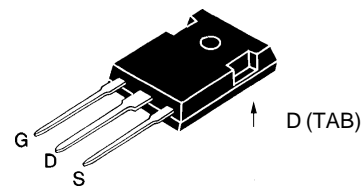
N-Channel Enhancement Mode
 Avalanche Rated, High dv/dt, Low t_{rr}



Preliminary data

| Symbol | Test Conditions | Maximum Ratings | |
|-----------|---|-----------------|------------------|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | 550 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$ | 550 | V |
| V_{GS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 22 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, pulse width limited by T_{JM} | 88 | A |
| I_{AR} | $T_C = 25^\circ\text{C}$ | 22 | A |
| E_{AR} | $T_C = 25^\circ\text{C}$ | 30 | mJ |
| dv/dt | $I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$ | 5 | V/ns |
| P_D | $T_C = 25^\circ\text{C}$ | 300 | W |
| T_J | | -55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +150 | $^\circ\text{C}$ |
| T_L | 1.6 mm (0.063 in) from case for 10 s | 300 | $^\circ\text{C}$ |
| M_d | Mounting torque | 1.13/10 | Nm/lb.in. |
| Weight | | 6 | g |

TO-247 AD



G = Gate, D = Drain,
 S = Source, TAB = Drain

Features

- International standard packages JEDEC TO-247 AD
- Low $R_{DS(\text{on})}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance (< 5 nH)
 - easy to drive and to protect
- Fast intrinsic Rectifier

Applications

- Power Factor Control Circuits
- Uninterruptible Power Supplies (UPS)
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls
- Low voltage relays

Advantages

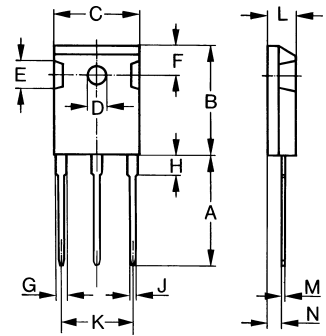
- Easy to mount with 1 screw (isolated mounting screw hole)
- Space savings
- High power density

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|---------------------|--|---|------|---------------------------|
| | | min. | typ. | max. |
| V_{DSS} | $V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$ | 550 | | V |
| $V_{GS(\text{th})}$ | $V_{DS} = V_{GS}$, $I_D = 4 \text{ mA}$ | 2 | | 4.5 V |
| I_{GSS} | $V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$ | | | $\pm 100 \text{ nA}$ |
| I_{DSS} | $V_{DS} = 0.8 \cdot V_{DSS}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$ | | | 250 μA 1 mA |
| $R_{DS(\text{on})}$ | $V_{GS} = 10 \text{ V}$, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$ | | | 0.27 Ω |

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | | |
|--------------|---|---|------|------|----|
| | | min. | typ. | max. | |
| g_{fs} | $V_{DS} = 10\text{ V}; I_D = 0.5 I_{D25}$, pulse test | 11 | 18 | S | |
| C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | | 4200 | pF | |
| C_{oss} | | | 450 | pF | |
| C_{rss} | | | 135 | pF | |
| $t_{d(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}, R_G = 2\ \Omega$ (External) | | 20 | 40 | ns |
| t_r | | | 43 | 60 | ns |
| $t_{d(off)}$ | | | 70 | 90 | ns |
| t_f | | | 40 | 60 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ | | 150 | 170 | nC |
| Q_{gs} | | | 29 | 40 | nC |
| Q_{gd} | | | 60 | 85 | nC |
| R_{thJC} | | | 0.42 | K/W | |
| R_{thCK} | | 0.15 | | K/W | |

Source-Drain Diode

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|----------|--|---|------|------------------|
| | | min. | typ. | max. |
| I_S | $V_{GS} = 0\text{ V}$ | | | 22 A |
| I_{SM} | Repetitive; pulse width limited by T_{JM} | | | 88 A |
| V_{SD} | $I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\delta \leq 2\%$ | | | 1.5 V |
| t_{rr} | $I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$ $T_J = 125^\circ\text{C}$ | | | 250 ns 400 ns |

TO-247 AD Outline


| Dim. | Millimeter | | Inches | |
|------|------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 19.81 | 20.32 | 0.780 | 0.800 |
| B | 20.80 | 21.46 | 0.819 | 0.845 |
| C | 15.75 | 16.26 | 0.610 | 0.640 |
| D | 3.55 | 3.65 | 0.140 | 0.144 |
| E | 4.32 | 5.49 | 0.170 | 0.216 |
| F | 5.4 | 6.2 | 0.212 | 0.244 |
| G | 1.65 | 2.13 | 0.065 | 0.084 |
| H | - | 4.5 | - | 0.177 |
| J | 1.0 | 1.4 | 0.040 | 0.055 |
| K | 10.8 | 11.0 | 0.426 | 0.433 |
| L | 4.7 | 5.3 | 0.185 | 0.209 |
| M | 0.4 | 0.8 | 0.016 | 0.031 |
| N | 1.5 | 2.49 | 0.087 | 0.102 |

Fig. 1 Output Characteristics

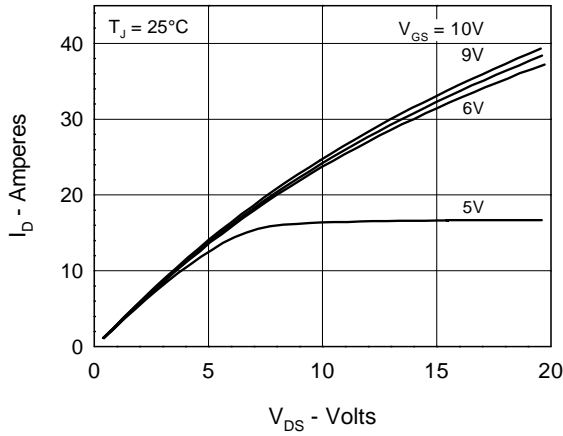


Fig. 2 Input Admittance

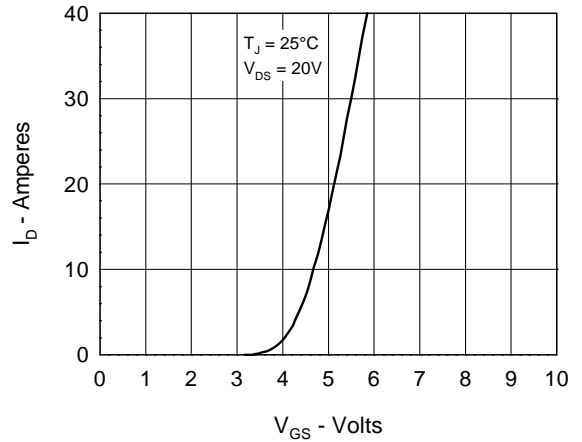


Fig. 3 $R_{DS(on)}$ vs. Drain Current

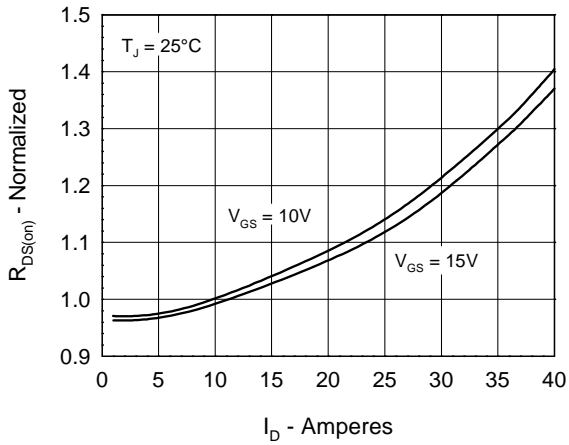


Fig. 4 Temperature Dependence of Drain to Source Resistance

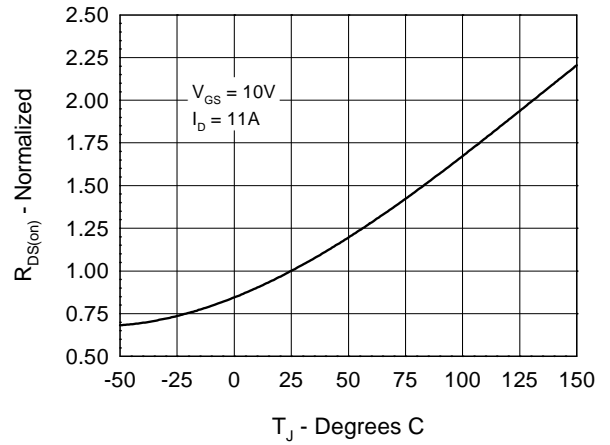


Fig. 5 Drain Current vs. Case Temperature

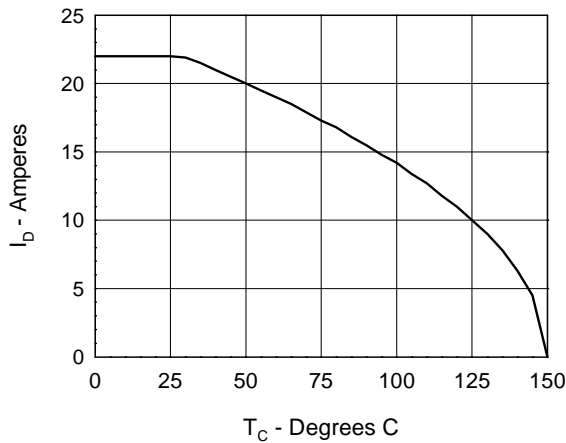


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

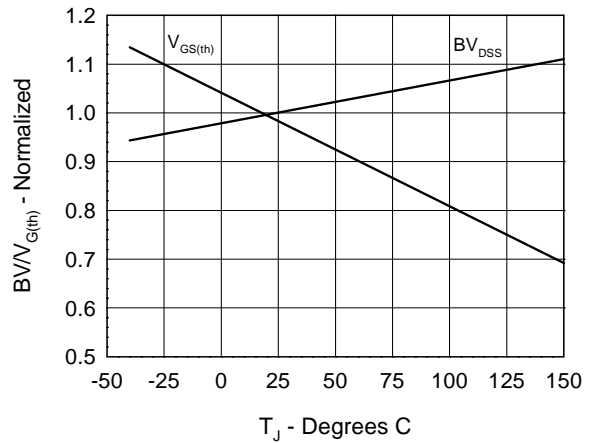


Fig.7 Gate Charge Characteristic Curve

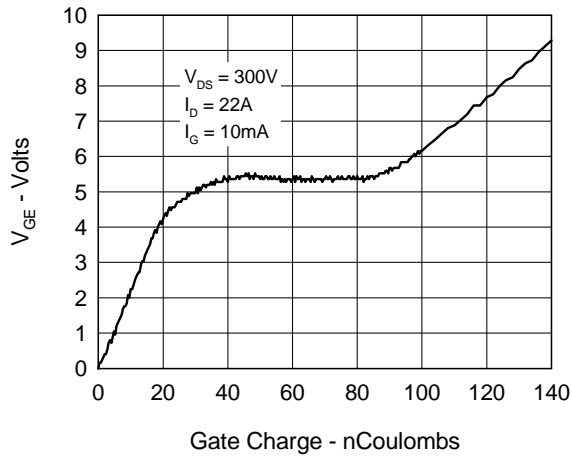


Fig.8 Forward Bias Safe Operating Area

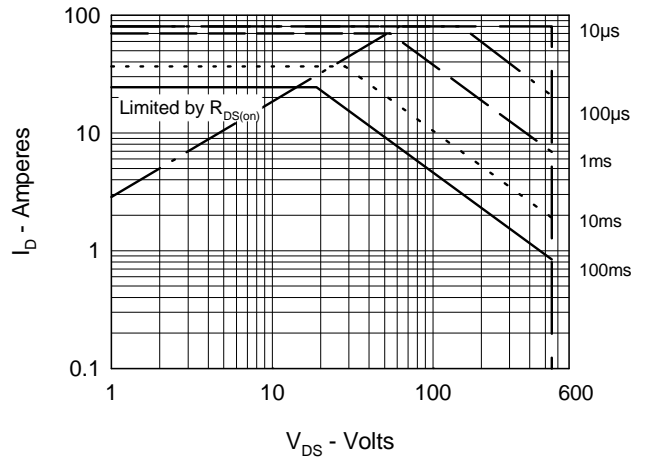


Fig.9 Capacitance Curves

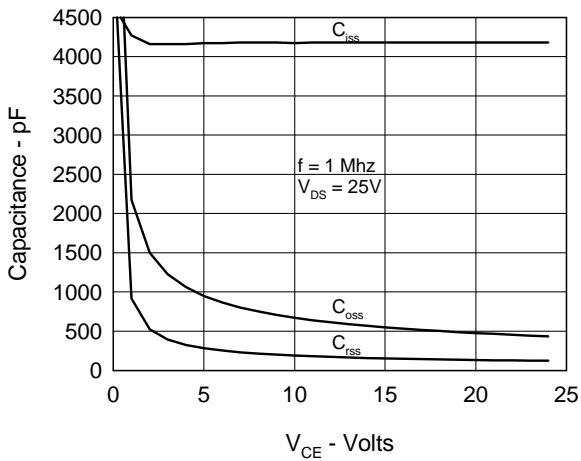


Fig.10 Source Current vs. Source to Drain Voltage

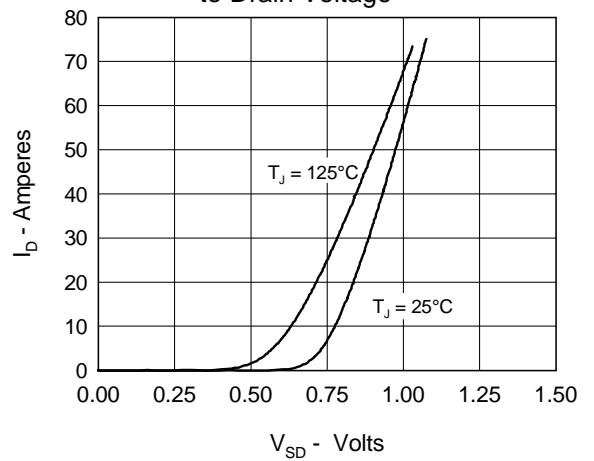


Fig.11 Transient Thermal Impedance

